

1. Material Substrate GaAs (N Type)
Epitaxial Layer GaAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

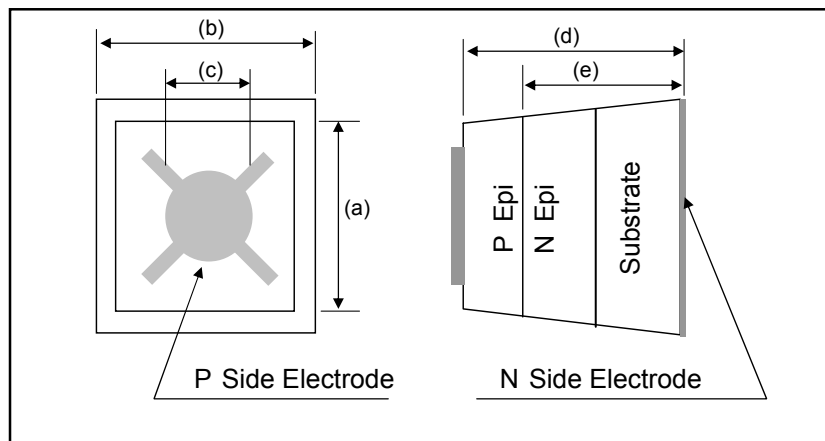
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$			1.3	V	IF=20mA
	$V_{F(2)}$			1.57	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	8	11		mW	IF=100mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

- (a) Emission Area ----- 10.5mil x 10.5mil
- (b) Bottom Area ----- 11.5mil x 11.5mil
- (c) Bonding Pad ----- 130um
- (d) Chip Thickness ----- 7mil
- (e) Junction Height ----- 4.7mil



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